

MICRO

ELECTRONICS

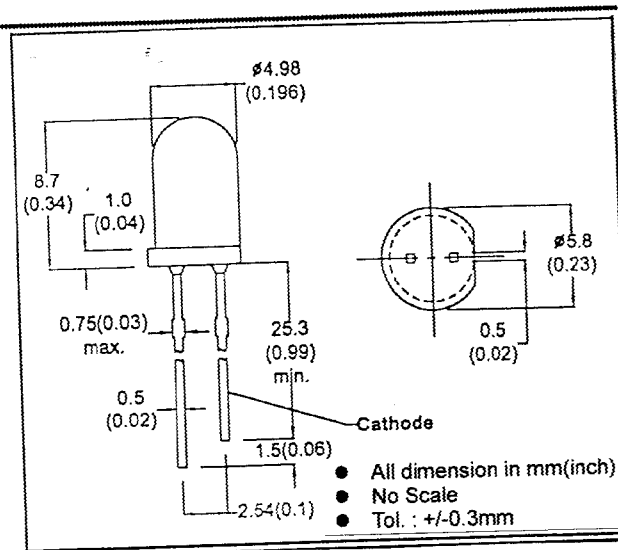
MIB57T-K

INFRARED
EMITTING
DIODE

DESCRIPTION

MIB57T-K is a GaAlAs infrared emitting diode molded in clear plastic 5mm diameter package. With the lensing effect of the package.

MIB57T-K is spectrally matched to the PIN photo diode ML303.



ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	150mW
Operating Temperature Range	-40 to +100°C
Lead Soldering Temperature (1/16" from body)	260°C

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTI (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po	2.62	4.5		mW	IF=20mA
Forward Voltage	VF		1.2	1.6	V	IF=100mA
Reverse Current	IR			10	μA	VR=5V
Peak Wavelength	λp		940		nm	IF=20mA
Spectrum Line Half Width	Δλ		45		nm	IF=20mA



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

MIB57T-K

